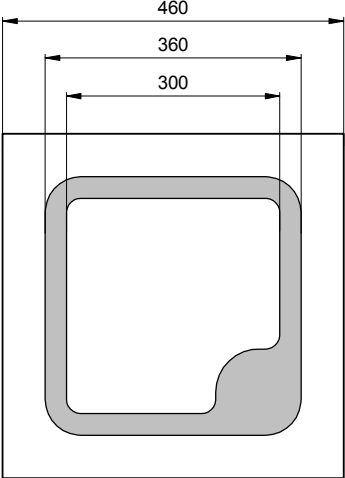


Wavelength range	Type	Technology	Electrodes
Red, selective	Integrated filter	AlGaAs/GaAs	P (anode) up

	typ. dimensions (µm)	
	<u>typ. thickness</u> 260 (±25) µm <u>anode</u> gold alloy, 1.5 µm <u>cathode</u> gold alloy, 0.5 µm	Description Narrow response range (660 nm peak) Applications Optical communications, safety equipment, light barriers

Miscellaneous ParametersT_{amb} = 25°C, unless otherwise specified

Parameter	Test conditions	Symbol	Value	Unit
Active area		A	0,17	mm ²
Operating temperature range		T _{amb}	-40 to +125	°C
Storage temperature range		T _{stg}	-40 to +125	°C

Optical and Electrical CharacteristicsT_{amb} = 25°C, unless otherwise specified

Parameter	Test conditions	Symbol	Min	Typ	Max	Unit
Peak sensitivity wavelength	V _R = 0 V	λ _p		660		nm
Spectral range at 50 %	V _R = 0 V	λ _{0.5}	620		700	nm
Responsivity at λ _p ¹	V _R = 0 V	S _λ		0.20		A/W
Responsivity at λ _p ²	V _R = 0 V	S _λ		0.42		A/W
Spectral bandwidth at 50%	V _R = 0 V	Δλ _{0.5}		80		nm
Dark current	V _R = 1 V	I _D		40	200	pA
Junction capacitance	V _R = 0 V	C _J		40		pF
Switching time	V _R = 1 V	t _r , t _f		15/30		ns

¹Measured on bare chip on TO-18 header²Measured on epoxy covered chip on TO-18 header**Labeling**

Type	Typ. I _D [pA]	Typ. S _λ [A/W]	Lot N°	Quantity
EPC-660-0.5				

Packing: Chips on adhesive film with wire-bond side on top*Note: All measurements carried out with *EPIGAP* equipment

Typical responsivity spectrum